

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	66	((wir\$3 conduct\$3 metal\$3) near (layer film)) near2: extend\$3 near2 over near2 substrate	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2004/12/24 11:07
L2	0	((low near resistance) near (layer film)) near2 extend\$3 near2 over near2 substrate	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2004/12/24 11:08
L3	10793	(low near resistance) near2 (layer film)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2004/12/24 11:08
L4	47	3 and (extend\$3 near2 over near2 substrate)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2004/12/24 11:09
L5	8	("4710398" "4777061" "4804560" "4902645" "4917759" "5227336" "5270254" "5332693").PN	US-PGPUB; USPAT; USOCR	OR	ON	2004/12/24 11:21
S1	11685	257/347-354,507,545,69,195,204,206,338,357-359,365-377.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2004/12/23 17:10
S2	19	S1 and ((low near resistance near (wir\$3 metal\$3 conduct\$3)) with substrate)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2004/12/23 17:27
S3	6	("4478655" "5145802" "5286670" "5294821" "5479048" "5654573").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2004/12/23 17:19
S4	1	S1 and (low near resistance near (buried embeded) near (wir\$3 metal\$3 conduct\$3))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2004/12/23 17:31

S5	374502	"257"/\$.ccls. "438"/\$.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2004/12/23 17:30
S6	0	S5 and ((low near resistance near (buried embeded) near (wir\$3 metal\$3 conduct\$3)) with substrate)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2004/12/23 17:31
S7	3	S5 and (low near resistance near (buried embeded) near (wir\$3 metal\$3 conduct\$3))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2004/12/23 17:33
S8	1965	S5 and (low near resistance near (wir\$3 metal\$3))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2004/12/23 17:34
S9	214	S5 and ((low near resistance near (wir\$3 metal\$3)) with substrate)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2004/12/23 17:38
S10	9	S9 and SOI	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2004/12/23 17:39
S11	4116	S5 and (((Al aluminum (low near resistance)) near (wir\$3 metal\$3)) with substrate)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2004/12/23 17:43
S12	138	S11 and SOI	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2004/12/23 18:31
S13	1	S5 and (((Al aluminum (low near resistance)) near (buried embeded) near (wir\$3 metal\$3)) with substrate)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2004/12/23 17:44

S14	23	S5 and ((Al aluminum (low near resistance)) near (buried embeded) near (wir\$3 metal\$3))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2004/12/23 18:19
S15	47	((Al aluminum (low near resistance)) near (buried embeded) near (wir\$3 metal\$3))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2004/12/23 18:37
S16	12	("5311039").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	OFF	2004/12/23 18:28
S17	59	S11 and (junction near capacitance)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2004/12/23 18:32
S18	147920	((Al aluminum (low near resistance)) near (wir\$3 metal\$3))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2004/12/23 18:37
S19	75	S18 and ((buried embeded) near5 extend\$3 near5 substrate)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2004/12/23 18:41
S20	2758	extend\$3 near2 over near2 substrate	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2004/12/24 11:08
S21	266	S18 and S20	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2004/12/23 19:04
S22	786	S20 and ((metal\$3 wir\$3 Al) near (layer film))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2004/12/23 19:02

S23	168	S22 and ((semiconductor element circuit) near (region\$1 area\$1))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2004/12/23 18:53
S24	551	((buried embeded) near (metal\$3 wir\$3 Al) near (layer film))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2004/12/23 19:05
S25	1	S24 and S20	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2004/12/23 19:04
S26	1	((buried embeded) near (metal\$3 wir\$3 Al) near (layer film)) with (power near source)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2004/12/23 19:06
S27	1	((buried embeded) near (metal\$3 wir\$3 Al) near (layer film)) with (substrate near potential)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2004/12/23 19:07